

MJL4302AG Datasheet

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DiGi Electronics Part Number

MJL4302AG-DG

Manufacturer

onsemi

Manufacturer Product Number

MJL4302AG

Description

TRANS PNP 350V 15A TO264

Detailed Description

Bipolar (BJT) Transistor PNP 350 V 15 A 35MHz 230

W Through Hole TO-264



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DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MJL4302AG	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	15 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
350 V	1V @ 800mA, 8A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100μΑ	80 @ 5A, 5V
Power - Max:	Frequency - Transition:
230 W	35MHz
Operating Temperature:	Mounting Type:
-65°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-264-3, TO-264AA	TO-264
Base Product Number:	
MII 4202	

Environmental & Export classification

8541.29.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	Not Applicable
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



Complementary NPN-PNP Silicon Power Bipolar Transistors

MJL4281A (NPN) MJL4302A (PNP)

The MJL4281A and MJL4302A are power transistors for high power audio.

Features

- 350 V Collector-Emitter Sustaining Voltage
- Gain Complementary:

Gain Linearity from 100 mA to 5 A High Gain – 80 to 240 $h_{FE} = 50$ (min) @ $I_C = 8$ A

- Low Harmonic Distortion
- High Safe Operation Area 1.0 A/100 V @ 1 Second
- High f₇
- Pb-Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	350	Vdc
Collector-Base Voltage	V _{CBO}	350	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector-Emitter Voltage - 1.5 V	V _{CEX}	350	Vdc
Collector Current - Continuous - Peak (Note 1)	I _C	15 30	Adc
Base Current - Continuous	Ι _Β	1.5	Adc
Total Power Dissipation @ T _C = 25°C Derate Above 25°C	P _D	230 1.84	°C/W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

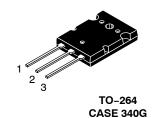
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.54	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

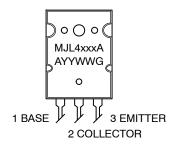
1. Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.

15 AMPERES COMPLEMENTARY SILICON POWER TRANSISTORS 350 VOLTS, 230 WATTS



MARKING DIAGRAM

STYLE 2



xxx = 281 or 302

A = Assembly Location

YY = Year

WW = Work Week

G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJL4281A	TO-264	25 Units/Rail
MJL4281AG	TO-264 (Pb-Free)	25 Units/Rail
MJL4302A	TO-264	25 Units/Rail
MJL4302AG	TO-264 (Pb-Free)	25 Units/Rail

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJL4281A (NPN) MJL4302A (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•		
Collector Emitter Sustaining Voltage (I _C = 50 mA, I _B = 0)	V _{CE(sus)}	350		Vdc
Collector Cut-off Current (V _{CE} = 200 V, I _B = 0)	I _{CEO}		100	μAdc
Collector Cutoff Current (V _{CB} = 350 Vdc, I _E = 0)	Ісво	-	50	μAdc
Emitter Cutoff Current (V _{EB} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	5.0	μAdc
SECOND BREAKDOWN				
Second Breakdown Collector with Base Forward Biased (V _{CE} = 50 Vdc, t = 1.0 s (non-repetitive) (V _{CE} = 100 Vdc, t = 1.0 s (non-repetitive)	I _{S/b}	4.5 1.0		Adc
ON CHARACTERISTICS	•	1		
DC Current Gain	h _{FE}	80 80 80 80 50	250 250 250 250 250 - -	-
Collector-Emitter Saturation Voltage (I _C = 8.0 Adc, I _B = 0.8 Adc)	V _{CE(sat)}	-	1.0	Vdc
Emitter–Base Saturation Voltage $(I_C = 8.0 \text{ Adc}, I_B = 0.8 \text{ A})$	V _{BE(sat)}	-	1.4	Vdc
Base-Emitter ON Voltage (I _C = 8.0 Adc, V _{CE} = 5.0 Vdc)	V _{BE(on)}	-	1.5	Vdc
DYNAMIC CHARACTERISTICS	<u>.</u>			
Current-Gain - Bandwidth Product (I _C = 1.0 Adc, V _{CE} = 5.0 Vdc, f _{test} = 1.0 MHz)	f _T	35	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1.0 MHz)	C _{ob}	-	600	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

MJL4281A (NPN) MJL4302A (PNP)

TYPICAL CHARACTERISTICS

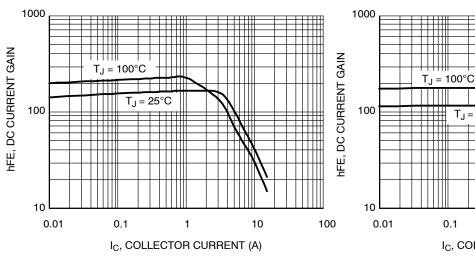


Figure 1. DC Current Gain, $V_{CE} = 5 \text{ V}$, NPN MJL4281A

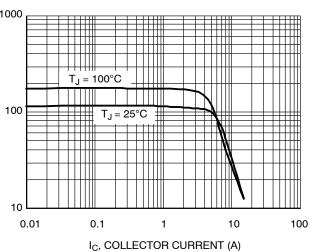


Figure 2. DC Current Gain, V_{CE} = 5 V, PNP MJL4302A

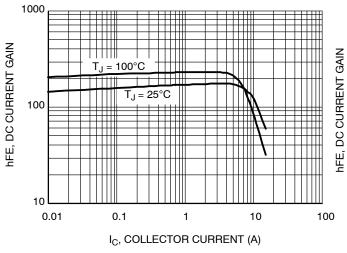


Figure 3. DC Current Gain, V_{CE} = 20 V, NPN MJL4281A

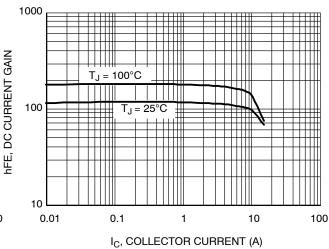


Figure 4. DC Current Gain, V_{CE} = 20 V, PNP MJL4302A

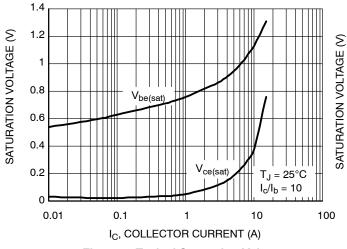


Figure 5. Typical Saturation Voltage, NPN MJL4281A

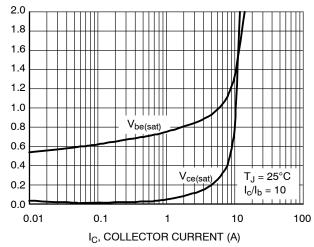


Figure 6. Typical Saturation Voltage, PNP MJL4302A

MJL4281A (NPN) MJL4302A (PNP)

TYPICAL CHARACTERISTICS

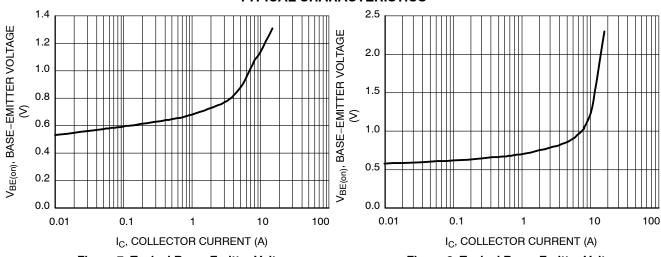


Figure 7. Typical Base-Emitter Voltages, NPN MJL4281A

Figure 8. Typical Base-Emitter Voltages, PNP MJL4302A

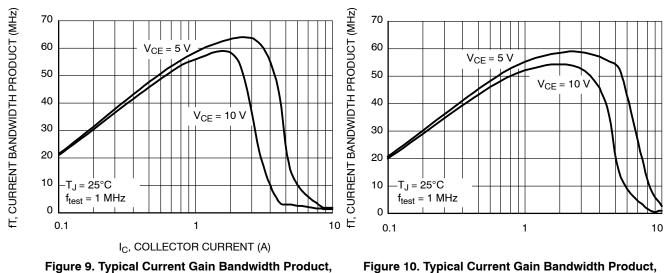


Figure 9. Typical Current Gain Bandwidth Product, NPN MJL4281A

100 100 10 mS Ic, COLLECTOR CURRENT (A) COLLECTOR CURRENT (A) 10 10 1 Sec 1 Sec 100 mS 100 mS 0.1 0.1 Ö $T_J = 25^{\circ}C$ 0.01 0.01 10 100 1000 10 100 1000 V_{ce}, COLLECTOR-EMITTER VOLTAGE (V) V_{ce}, COLLECTOR-EMITTER VOLTAGE (V)

Figure 11. Active Region Safe Operating Area, NPN MJL4281A

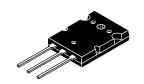
Figure 12. Active Region Safe Operating Area, PNP MJL4302A

PNP MJL4302A



MECHANICAL CASE OUTLINE

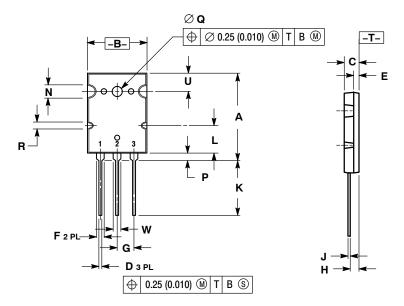
PACKAGE DIMENSIONS



TO-3BPL (TO-264) CASE 340G-02 ISSUE J

DATE 17 DEC 2004

SCALE 1:2



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	28.0	29.0	1.102	1.142
В	19.3	20.3	0.760	0.800
С	4.7	5.3	0.185	0.209
D	0.93	1.48	0.037	0.058
E	1.9	2.1	0.075	0.083
F	2.2	2.4	0.087	0.102
G	5.45 BSC		0.215 BSC	
Н	2.6	3.0	0.102	0.118
J	0.43	0.78	0.017	0.031
K	17.6	18.8	0.693	0.740
L	11.2 REF		0.411 REF	
N	4.35 REF		0.172 REF	
Р	2.2	2.6	0.087	0.102
Q	3.1	3.5	0.122	0.137
R	2.25 REF		0.089	REF
U	6.3	6.3 REF		REF
W	2.8	3.2	0.110	0.125

GENERIC MARKING DIAGRAM*

STYLE 1	:
PIN 1.	GATE
2	DRAIN

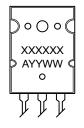
3. SOURCE

STYLE 2: PIN 1. BASE

E 2: 1. BASE 2. COLLECTOR 3. EMITTER STYLE 3: PIN 1. GATE 2. SOURCE

GATE SOURCE DRAIN

STYLE 4: PIN 1. DRAIN 2. SOURCE 3. GATE STYLE 5: PIN 1. GATE 2. COLLECTOR 3. EMITTER



XXXXXX = Specific Device Code

A = Location Code

YY = Year WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

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